

D3

G3

S3D4

G4 S4

# **RF POWER MOSFET FULL-BRIDGE**

The ARF1510 is four RF power transistor arranged in an H-Bridge configuration. It is intended for off-line 300V operation in high power scientific, medical and, industrial RF power generator and amplifier applications up to 40 MHz.

• Specified 300 Volt, 27.12 MHz Characteristics:

- Output Power = 750 Watts.
- Gain = 17dB (Class D)
- Efficiency > 80%

- High Performance Power RF Package.
- Very High Breakdown for Improved Ruggedness.
- Low Thermal Resistance.
- Nitride Passivated Die for Improved Reliability.

MAXIMUN	<b>IRATINGS</b> All Ratings Per Die: T <sub>C</sub>	Per Die: $T_{C} = 25^{\circ}C$ unless otherwise specified.				
Symbol	Parameter	ARF 1510	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	1000	Volts			
Ι <sub>D</sub>	Continuous Drain Current @ T <sub>C</sub> = 25°C	6.5	Amps			
V <sub>GS</sub>	Gate-Source Voltage	±30	Volts			
P <sub>D</sub>	Total Device Dissipation @ $T_{C} = 25^{\circ}C$	1500	Watts			
T <sub>J</sub> ,T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to 200	°C			
TL	Lead Temperature: 0.063" from Case for 10 Sec.	300				

## STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage ( $V_{GS} = 0V$ , $I_{D} = 250 \mu A$ )	1000			Valta	
V <sub>DS(ON)</sub>	On State Drain Voltage $(I_{D(ON)} = 3.25A, V_{GS} = 10V)$		6.8	7.5	Volts	
1	Zero Gate Voltage Drain Current (V <sub>DS</sub> = 1000V, V <sub>GS</sub> = 0V)			25	μA	
'DSS	Zero Gate Voltage Drain Current ( $V_{DS} = 800V, V_{GS} = 0V, T_{C} = 125^{\circ}C$ )			250		
I <sub>GSS</sub>	Gate-Source Leakage Current ( $V_{GS} = \pm 30V$ , $V_{DS} = 0V$ )			±100	nA	
9 <sub>fs</sub>	Forward Transconductance ( $V_{DS} = 25V, I_{D} = 3.25A$ )	3	4		mhos	
V <sub>isolation</sub>	RMS Voltage (60Hz Sinewave from terminals to mounting surface for 1 minute)	2500			Volts	
V <sub>GS(TH)</sub>	Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 50$ mA)	3		5	Volts	

## THERMAL CHARACTERISTICS

Symbol	Characteristic (per package unless otherwise noted)		ТҮР	МАХ	UNIT
$R_{_{ ext{ heta}JC}}$	Junction to Case			0.12	0000
$R_{_{\!  ext{ heta}CS}}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planar Heat Sink Surface.)		0.08		°C/W

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

#### **DYNAMIC CHARACTERISTICS**

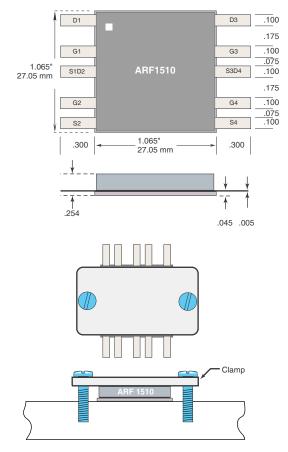
Symbol	Characteristic	Test Conditions	MIN	ТҮР	МАХ	UNIT
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V		1200	1800	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 200V		100	130	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		20	26	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = 15V		8		
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 500V		5		ns
t <sub>d(off)</sub>	Turn-off Delay Time	l <sub>D</sub> = 6.5A @ 25°C		18		115
t <sub>f</sub>	Fall Time	R <sub>G</sub> = 1.6 Ω		10		

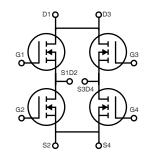
#### FUNCTIONAL CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	ТҮР	МАХ	UNIT
G <sub>PS</sub>	Common Source Amplifier Power Gain	f = 40.7 MHz	13	15		dB
η	Drain Efficiency	$V_{GS} = 0V$ $V_{DD} = 400V$		75		%
Ψ	Electrical Ruggedness VSWR 6:1	$P_{out} = 750W$	No Degradation in Output Powe			t Power

(1) Pulse Test: Pulse width < 380  $\mu$ S, Duty Cycle < 2%.

APT Reserves the right to change, without notice, the specifications and information contained herein.





#### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and mounting surface is beryllium oxide, BeO. Beryllium oxide dust is toxic when inhaled. Care must be taken during handling and mounting to avoid damage to this area. These devices must never be thrown away with general industrial or domestic waste.

#### Thermal Considerations and Package Mounting:

The rated 1500W power dissipation is only available when the package mounting surface is at 25°C and the junction temperature is 200°C. The thermal resistance between junctions and case mounting surface is 0.12°C/W. When installed, and additional thermal impedance of 0.08°C/W between the package base and the mounting surface is typical. Insure that the mounting surface is smooth and flat. Thermal joint compound must be used to reduce the effects of small surface irregularities. The heat sink should incorporate a copper heat spreader to obtain best results.

The package is designed to be clamped to a heatsink. A clamped joint maintains the required mounting pressure while allowing for thermal expansion of both the device and the heat sink. A simple clamp and two 6-32 (M3.5) screw can provide the minimum 125lb required mounting force. T = 12 in-lb.